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4	US 6563743 B2		USPAT	20030513	57

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Full

US 6563743 B2

**United States Patent**  
Hannwa et al.

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(4) SEMICONDUCTOR DEVICE HAVING DILIMIT CELLS AND SEMICONDUCTOR DEVICE HAVING DUMMY CELLS FOR RECEDANCY

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[?] ABSTRACT

A memory cell includes a plurality of thin memory cells MC for storing "1" or "0", arranged at points of intersection between a plurality of word lines W10 to W17 and a plurality of bit lines B10 to B17. A plurality of thin dummy cells MDC for storing "1" or "0" are arranged at points of intersection between the word lines W20 to W27 and a plurality of bit lines B10 to B17, and a plurality of non-thin dummy cells NDC for storing "1" or "0" are arranged at points of intersection between the word lines W28 to W35 and a plurality of bit lines B10 to B17. The non-thin dummy cells NDC have a larger area than the thin dummy cells MDC, so as to reduce the influence of leakage current between the word lines W28 to W35 and the bit lines B10 to B17.

[?] Claims, 23 Drawing Sheets